

IN THE SPECIFICATION

Please replace the fourth full paragraph on page 8 with the following paragraph:

Figure 4A illustrates an embodiment of a series switch 70 that uses a pair of beam arrays 72 similar to those shown in Figure 3B. The beam arrays 72 in the switch 70 are similar in construction of those used in the shunt switch 50. As in the switch 50 a pair of beam arrays is symmetrically positioned about a signal line 73, although in other embodiments the beam arrays 72 need not be symmetrically positioned about the signal line or, in other cases, only one beam array 72 may be needed to make the connection. In this series switch 70, however, the signal line 73 is not continuous but rather consists of a first portion 74 which is electrically insulated from a second portion 76. Moreover, in the series switch 70, the anchors 56 are not connected to ground, but instead are electrically insulated from the substrate so that current cannot travel through them to the substrate.

Please replace the third full paragraph on page 14 with the following paragraph:

Figures 9A through 9J illustrate an embodiment of a process for the construction of a composite beam switch, such as switch 110 (see Figure 6A). The method for making other embodiments of switches shown herein is an extension of this method. In Figure 9A, a dielectric material layer 192 such as silicon dioxide (SiO_2), silicon nitride (SiN) or silicon carbide (SiC) is deposited on top of another layer 190 such as polysilicon. In Figure 9B a bottom metal layer is deposited and patterned onto the top of the dielectric layer 192. A low

conductivity material, such as polysilicon, is preferred. In Figure 9C, a second dielectric layer 196 is deposited on top of the first dielectric layer 192 and the bottom metal layer 194, leaving a plurality of holes 198 in the second dielectric layer 196. In Figure 9D, a conductive layer 200 (e.g., gold) is applied on top of the second dielectric layer and the transmission lines 144 and electrodes 142 are patterned and etched. In Figure 9E a sacrificial layer ~~200~~ 202, which will later be removed to release the beam, is deposited and patterned so that it rests over the area between the dielectric pads 114 and 116. In Figure 9F, the dimple hole patterns 204 are etched into the sacrificial layer 202 and a liftoff alloying metal, such as titanium (Ti) or nickel (Ni), is deposited into the dimples. In Figure 9G one of the conductive layers 206 of the beam is deposited on top of the sacrificial layer, the dielectric layer, and the dimples. In Figure 9H, the structural layer 208 is deposited on top of the first conductive layer 206. In Figure 9I, the second conductive layer 210 is put on top of the structural layer 208, such that the structural layer 208 is now sandwiched between the first conductive layer 206 and the second conductive layer 210. The resulting structure is etched to create the anchors 118 and 120 and remove unwanted material from the wafer. Finally, in Figure 9J, the sacrificial layer remaining between the beam 122 and the substrate is removed, such that the beam 122 is released and is ready for operation.